



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Transistors

SOT-363

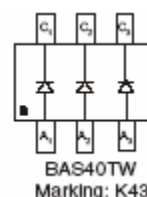
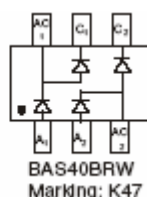
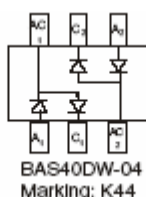
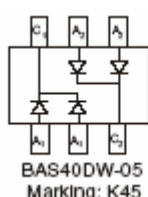
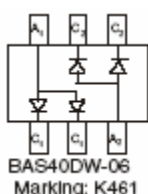


BAS40TW/DW-04/DW-05/DW-06/BRW

SCHOTTKY BARRIER DIODE ARRAYS

FEATURES

- Low Forward voltage drop
- Fast switching



Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	40	V
DC Blocking Voltage	V _R		
Average Rectified Output Current	I _O	200	mA
Power Dissipation	P _d	200	mW
Thermal Resistance. Junction to Ambient Air	R _{θJA}	625	°C/W
Junction temperature	T _J	-55-125	°C
Storage temperature range	T _{STG}	-65-125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR)	I _R = 10μA	40		V
Reverse voltage leakage current	I _R	V _R =30V		200	nA
Forward voltage	V _F	I _F =1mA I _F =40mA		380 1000	mV
Total capacitance	C _T	V _R =0, f=1MHz		5	pF
Reverse recovery time	t _{rr}	I _F =10mA, I _R =I _F =1mA R _L =100Ω		5	nS

